



FP304

TR:NPN Epitaxial Planar Silicon Transistor
SBD:Schottky Barrier Diode

DC-DC Converter

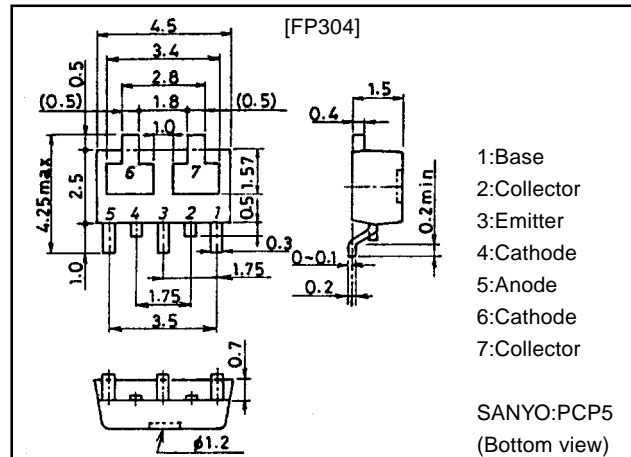
Features

- Complex type with an NPN transistor and a Schottky barrier diode facilitating high-density mounting.
- The FP304 is composed of 2 chips, one being equivalent to the 2SD1620 and the other the SB07-03C, placed in one package.

Package Dimensions

unit:mm

2099A

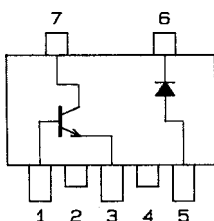


Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
[TR]				
Collector-to-Base Voltage	V_{CBO}		30	V
Collector-to-Emitter Voltage	V_{CEO}		10	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		3	A
Collector Current (Pulse)	I_{CP}		5	A
Base Current	I_B		500	mA
Collector Dissipation	P_C	Mounted on ceramic board (250mm \times 0.8mm)	0.8	W
Junction Temperature	T_J		150	°C
[SBD]				
Repetitive Peak Reverse Voltage	V_{RRM}		30	V
Non-repetitive Peak Reverse Surge Voltage	V_{RSM}		35	V
Average Rectified Current	I_O		700	mA
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	5	A
Junction Temperature	T_J		-55 to +125	°C
Storage Temperature	T_{stg}		-55 to +125	°C

Electrical Connection



- 1:Base
- 2:Collector
- 3:Emitter
- 4:Cathode
- 5:Anode
- 6:Cathode
- 7:Collector

(Top view)

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FP304

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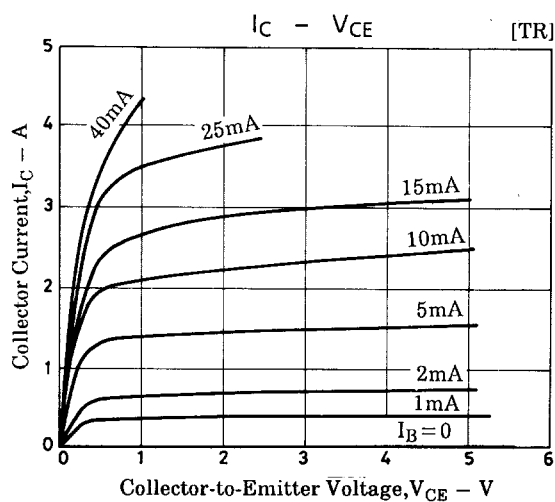
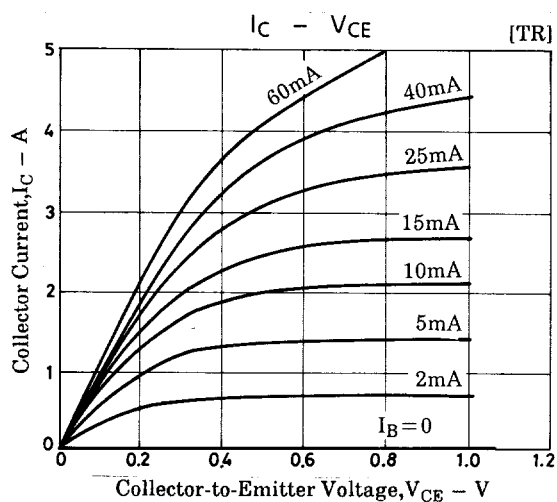
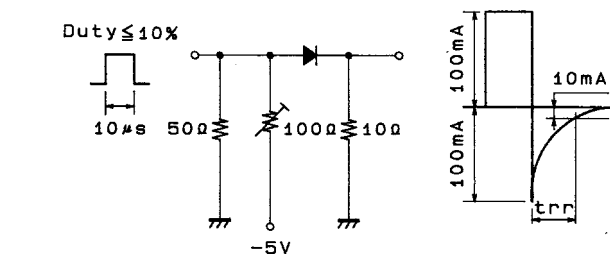
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[TR]						
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=2V, I_C=500mA$	200			
	h_{FE2}	$V_{CE}=2V, I_C=3A$	140			
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=50mA$		200		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		30		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=3A, I_B=60mA$		0.3	0.4	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=3A, I_B=60mA$		0.95	1.35	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	10			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
[SBD]						
Reverse Voltage	V_R	$I_R=300\mu A$	30			V
Forward Voltage	V_F	$I_F=700mA$			0.55	V
Reverse Current	I_R	$V_R=15V$			80	μA
Interterminal Capacitance	C	$V_R=10V, f=1MHz$		28		pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=100mA$, See specified Test Circuit.			10	ns
Thermal Resistance	R_{thj-a}	Mounted on ceramic board (250mm ² ×0.8mm)		170		°C/W

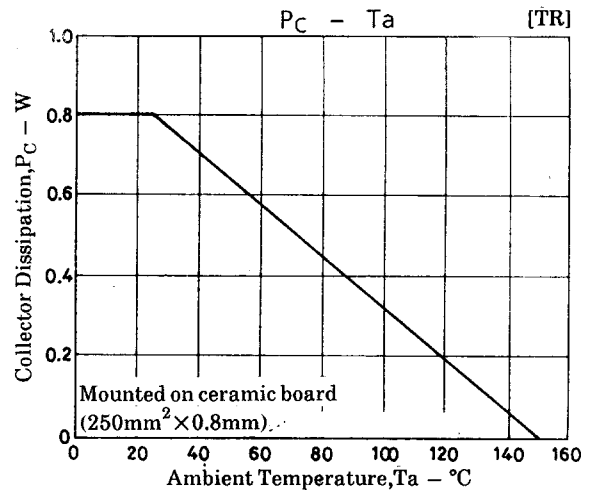
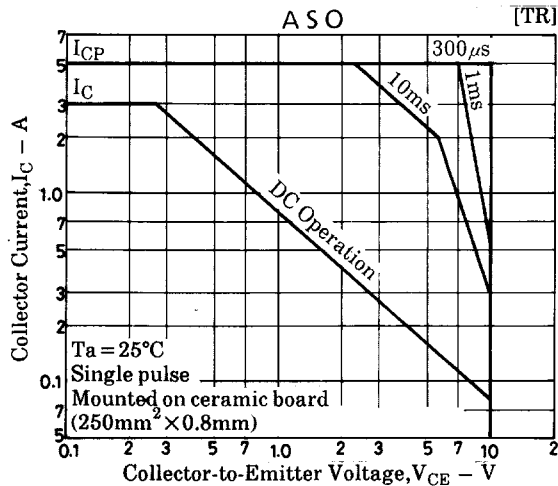
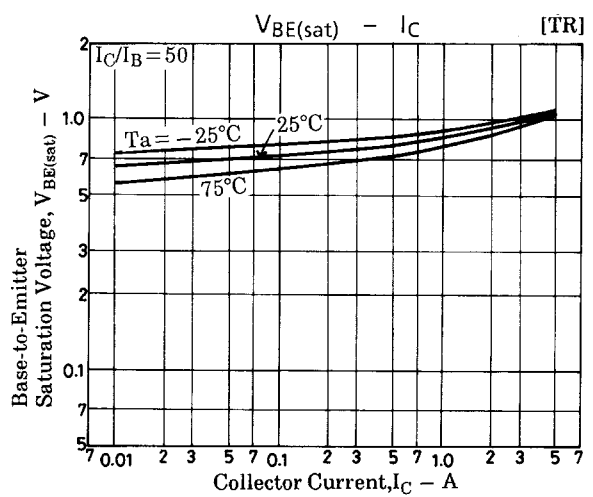
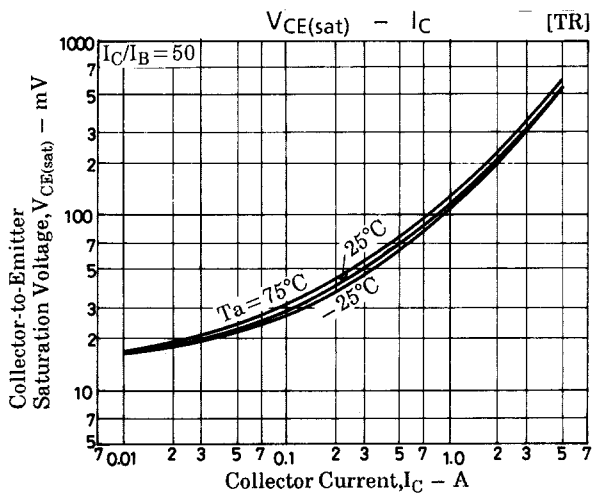
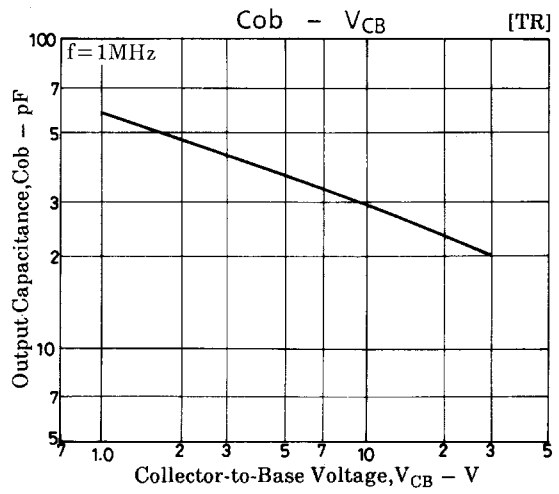
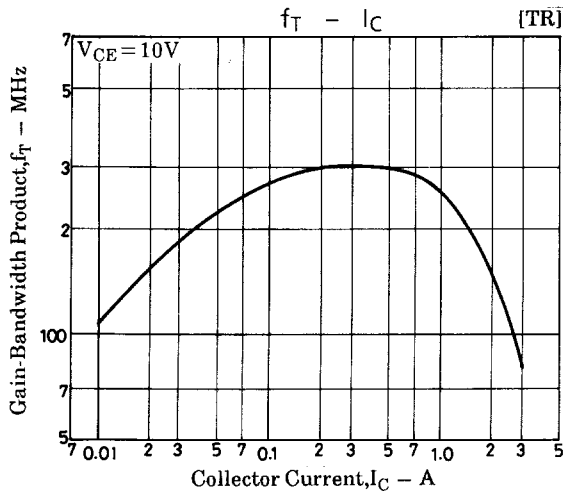
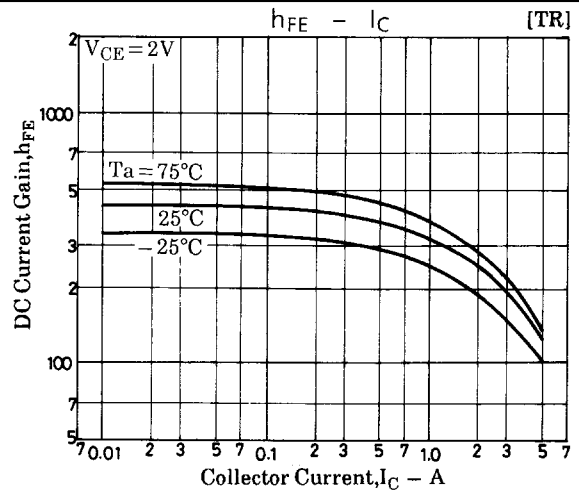
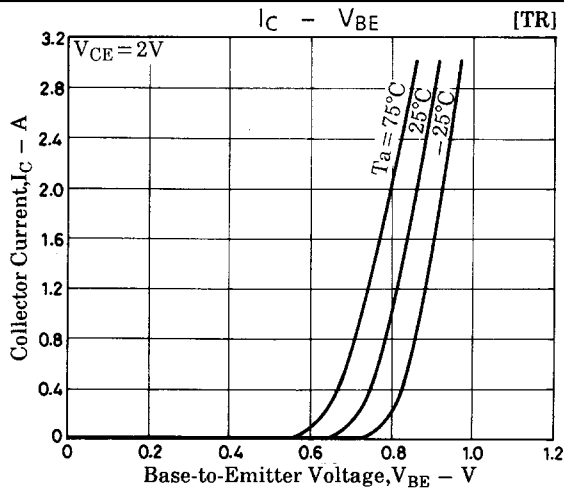
Marking:304

Switching Time Test Circuit

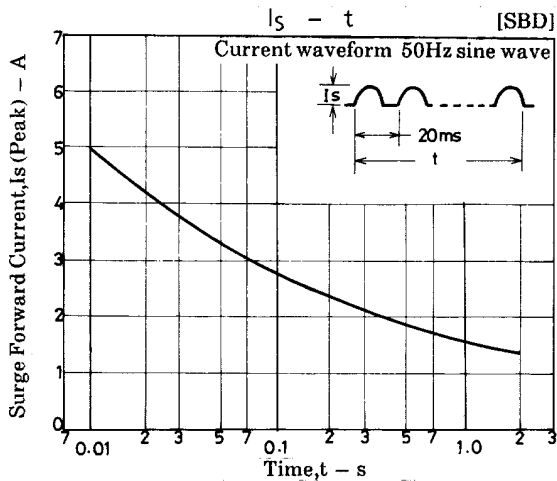
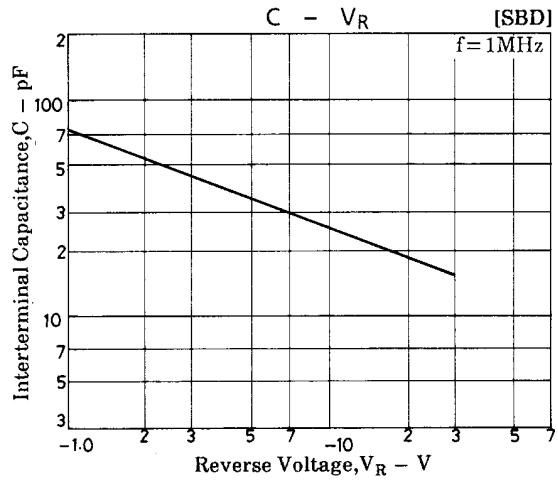
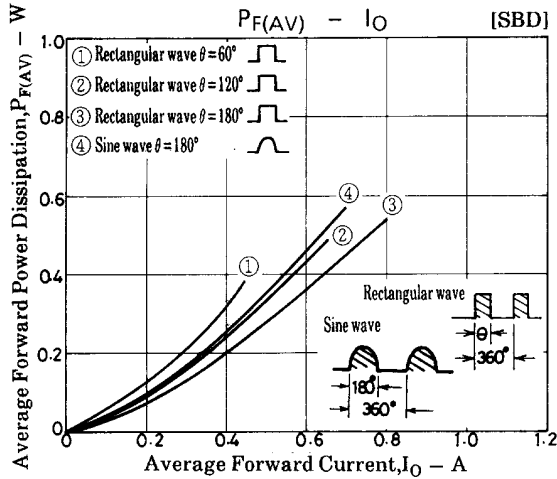
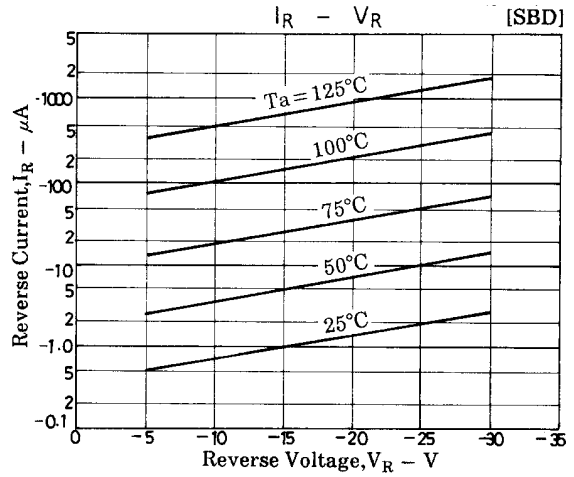
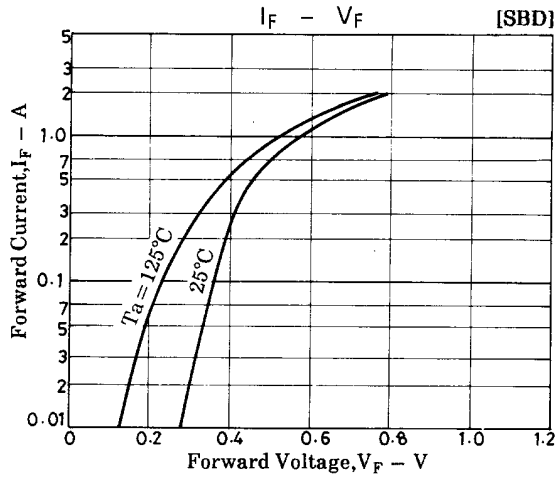
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